

Silicon NPN Power Transistors

2SD526

DESCRIPTION

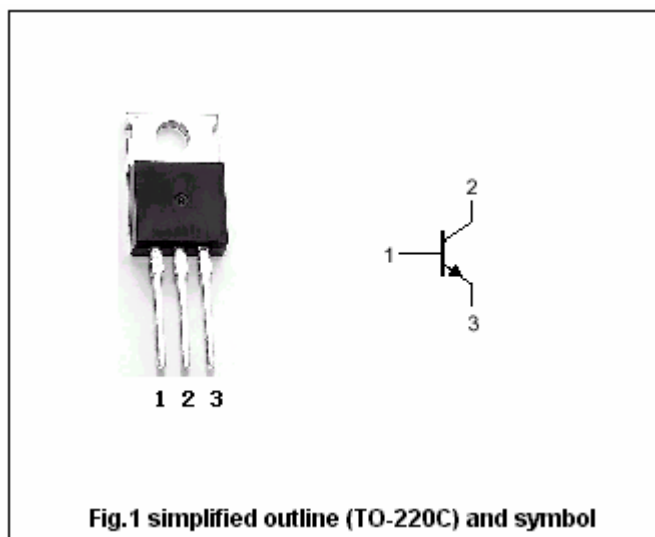
- With TO-220C package
- Complement to type 2SB596
- Good linearity of h_{FE}

APPLICATIONS

- Power amplifier applications
- Recommend for 20~25W high fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	80	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
I_B	Base current		0.4	A
P_C	Collector power dissipation	$T_C=25℃$	30	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA; I _B =0	80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3 A; I _B =0.3 A			1.5	V
V _{BE}	Base-emitter voltage	I _C =3A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =80V ; I _E =0			30	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μA
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =5V	40		240	
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =5V	15			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		8		MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz		90		pF

◆ h_{FE-1} classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

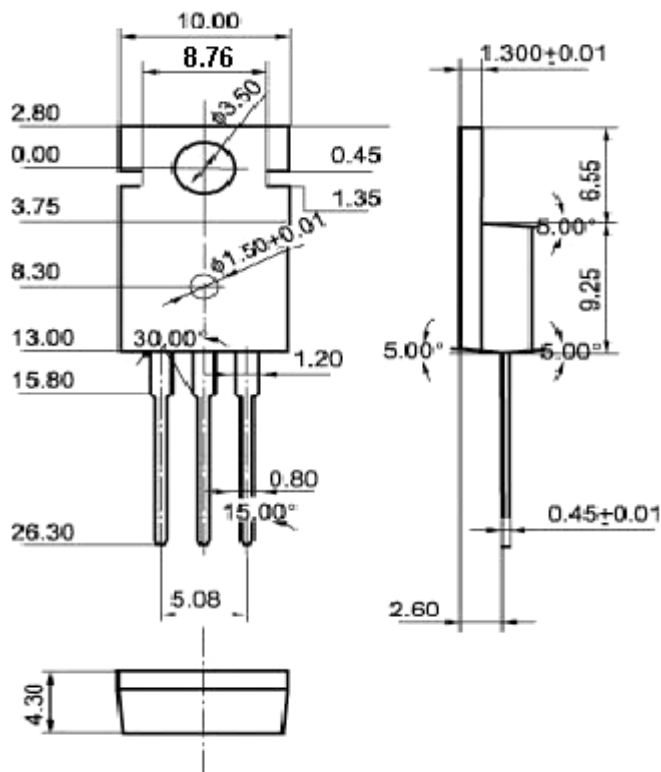


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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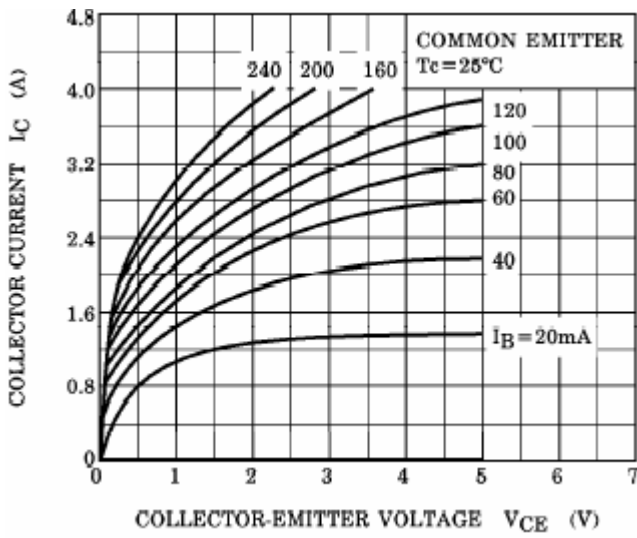


Fig.3 Static Characteristic

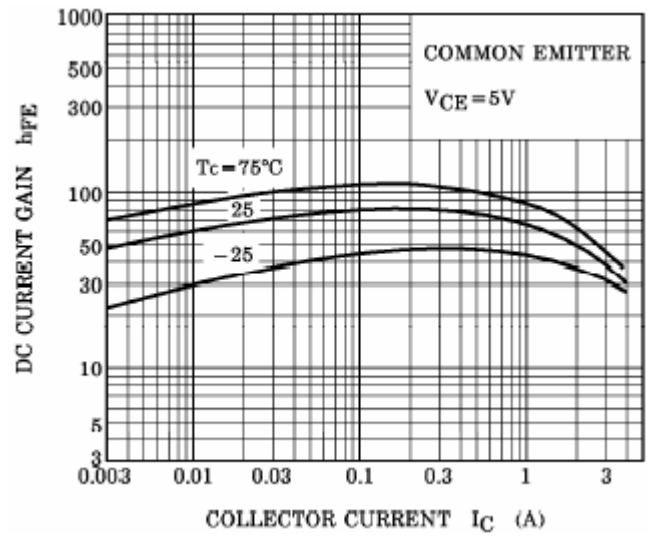


Fig.4 DC current Gain

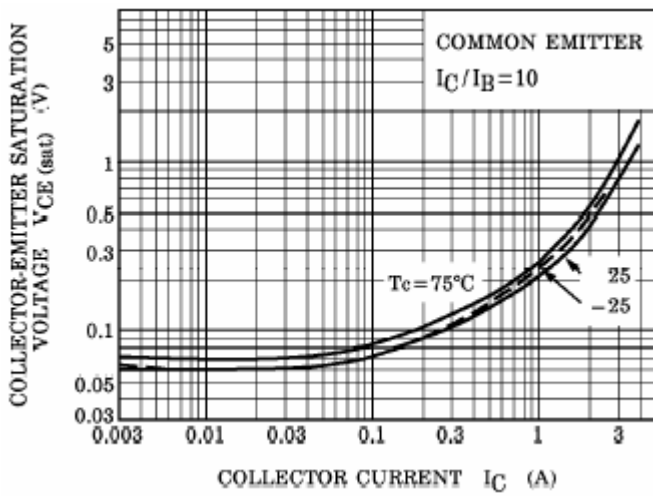


Fig.5 Collector-Emitter Saturation Voltage

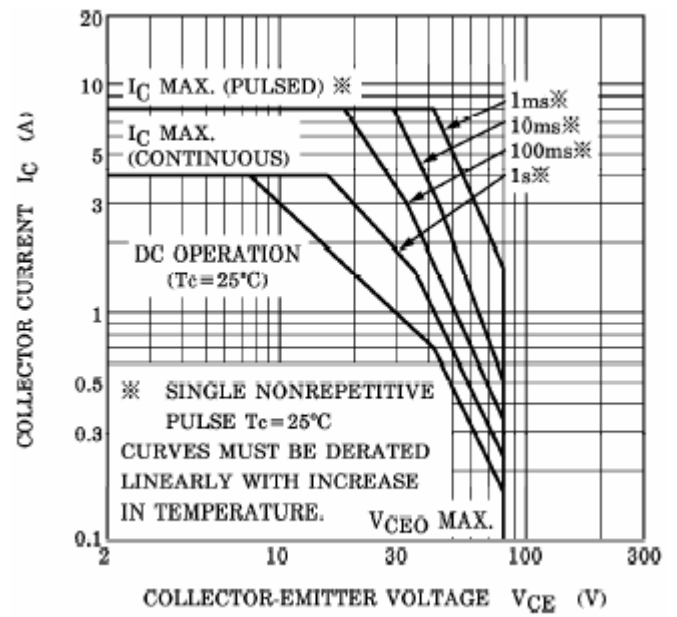


Fig.6 Safe Operating Area